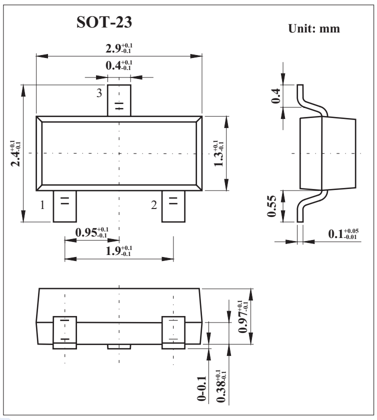
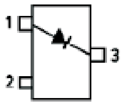
Silicon Epitaxial Planar Type

1SS370

■ Features

- ● Low forward voltage :$V_{F(3)}$ = 0.9 V(Typ)
- ● Fast reverse recovery time :t_{rr} = 60ns (MAX.)
- ● Small total capacitance :C_T = 1.5 pF(Typ)





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	250	V
Reverse voltage	V_R	200	V
Average forward current	I_O	100	mA
Maximum (peak) forward current	I_{FM}	300	mA
Surge current (10 ms)	I_{FSM}	2	A
Power dissipation	P	100	mW
Junction Temperature	T_j	125	℃
Storage Temperature	T_{stg}	-55 + 125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_{F(1)}$	I_F = 10 mA		0.72	1.0	V
	$V_{F(2)}$	I_F = 100 mA		0.90	1.2	
Reverse current	$I_{R(1)}$	V_R = 50 V			0.1	μ A
	$I_{R(2)}$	V_R = 200 V			1.0	
Total capacitance	C_T	V_R = 0, f = 1.0 MHz		1.5	3.0	pF
Reverse recovery time	t_{rr}	I_F = 10 mA		10	60	ns

■ Marking

Marking	F5